5.0 V, 3.3 V 450 mA Low-Dropout Voltage Regulator with Reset

The NCV4275A is an integrated low dropout regulator designed for use in harsh automotive environments. It includes wide operating temperature and input voltage ranges. The output is regulated at 5.0 V or 3.3 V and is rated to 450 mA of output current. It also provides a number of features, including overcurrent protection, overtemperature protection and a programmable microprocessor reset. The NCV4275A is available in the DPAK and D²PAK surface mount packages. The output is stable over a wide output capacitance and ESR range. The NCV4275A is pin for pin compatible with NCV4275.

Features

- 5.0 V and 3.3 V, ±2% Output Voltage Options
- 450 mA Output Current
- Very Low Current Consumption
- Active Reset Output
- Reset Low Down to $V_Q = 1.0 \text{ V}$
- 500 mV (max) Dropout Voltage
- Fault Protection
 - ♦ +45 V Peak Transient Voltage
 - → -42 V Reverse Voltage
 - Short Circuit Protection
 - ◆ Thermal Overload Protection
- AEC-Q100 Qualified
- Pin Compatible with NCV4275
- These are Pb-Free Devices

Applications

• Auto Body Electronics

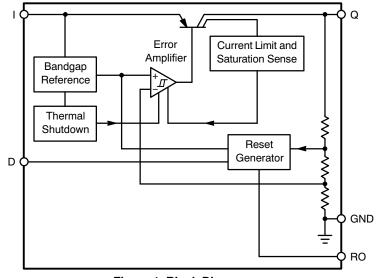


Figure 1. Block Diagram



ON Semiconductor®

http://onsemi.com



CASE 175AA



MARKING



D²PAK, 5-PIN DS SUFFIX CASE 936A



= 5 (5.0 V Output) or 3 (3.3 V Output)

A = Assembly Location

WL, L = Wafer Lot Y = Year WW = Work Week G = Pb-Free Package

Pin 1. I

2. RO Tab, 3. GND*

> 4. D 5. Q

* Tab is connected to Pin 3 on all packages

ORDERING INFORMATION

See detailed ordering and shipping information in the dimensions section on page 17 of this data sheet.

PIN FUNCTION DESCRIPTION

Pin#	Symbol	Description					
1	I	Input; Battery Supply Input Voltage. Bypass to ground with a ceramic capacitor.					
2	RO	Reset Output; Open Collector Active Reset (accurate when I > 1.0 V).					
3, Tab	GND	Ground; Pin 3 internally connected to tab.					
4	D	Reset Delay; timing capacitor to GND for Reset Delay function.					
5	Q	Output; $\pm 2.0\%$, 450 mA output. Bypass with 22 μ F capacitor, ESR < 4.5 Ω (5.0 V Version), 3.5 Ω (3.3 V Version) to ground.					

MAXIMUM RATINGS

Rating	Symbol	Min	Max	Unit
Input Voltage	VI	-42	45	V
Input Peak Transient Voltage	VI	-	45	V
Output Voltage	V _Q	-1.0	16	V
Reset Output Voltage	V _{RO}	-0.3	25	V
Reset Output Current	I _{RO}	-5.0	5.0	mA
Reset Delay Voltage	V _D	-0.3	7.0	V
Reset Delay Current	I _D	-2.0	2.0	mA
ESD Susceptibility (Note 1) - Human Body Model - Machine Model - Charge Device Model	ESD _{HBM} ESD _{MM} ESD _{CDM}	4.0 200 1000	- - -	kV V V
Junction Temperature	T _J	-40	150	°C
Storage Temperature	T _{stg}	-55	150	°C

Stresses exceeding Maximum Ratings may damage the device. Maximum Ratings are stress ratings only. Functional operation above the Recommended Operating Conditions is not implied. Extended exposure to stresses above the Recommended Operating Conditions may affect device reliability.

1. This device incorporates ESD protection and is tested by the following methods: ESD Human Body Model tested per AEC-Q100-002, ESD

^{1.} This device incorporates ESD protection and is tested by the following methods: ESD Human Body Model tested per AEC-Q100-002, ESD Machine Model tested per AEC-Q100-003, ESD Charged Device Model tested per AEC-Q100-011, Latch-up tested per AEC-Q100-004.

OPERATING RANGE

Input Voltage Operating Range, 5.0 V Output	VI	5.5	42	V
Input Voltage Operating Range, 3.3 V Output	VI	4.4	42	V
Junction Temperature	TJ	-40	150	°C

LEAD TEMPERATURE SOLDERING REFLOW AND MSL (Note 2)

Lead Free, 60 sec-150 sec above 217°C	T _{SLD}	-	265 Peak	°C
Moisture Sensitivity Level	MSL	1		

THERMAL CHARACTERISTICS

Characteristic	Test Conditions	Test Conditions (Typical Value)					
DPAK 5-PIN PACKAGE							
	Min Pad Board (Note 3)	1" Pad Board (Note 4)					
Junction-to-Tab (R _{0JT})	4.2	4.7	°C/W				
Junction-to-Ambient (R _{0JA})	100.9	46.8	°C/W				
D ² PAK 5-PIN PACKAGE	·		•				
	0.4 sq. in. Spreader Board (Note 5)	1.2 sq. in. Spreader Board (Note 6)					
Junction-to-Tab (R _{fl.IT})	3.8	4.0	°C/W				

74.8

41.6

°C/W

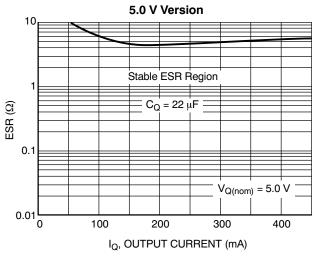
Junction-to-Ambient ($R_{\theta JA}$)

PR_R IPC / JEDEC J-STD-020C
 1 oz. copper, 0.26 inch² (168 mm²) copper area, 0.062" thick FR4.
 1 oz. copper, 1.14 inch² (736 mm²) copper area, 0.062" thick FR4.
 1 oz. copper, 0.373 inch² (241 mm²) copper area, 0.062" thick FR4.
 1 oz. copper, 1.222 inch² (788 mm²) copper area, 0.062" thick FR4.

ELECTRICAL CHARACTERISTICS (V_I = 13.5 V; -40° C < T_J < 150° C; unless otherwise noted.)

Characteristic	Symbol Test Conditions		5.0V Output Voltage			3.3V Output Voltage			Unit
				Тур	Max	Min	Тур	Max	
Output	•								•
Output Voltage	VQ	$ \begin{array}{l} 100 \; \mu A \leq I_Q \leq 400 \; mA \\ 6.0V \leq V_I \leq 28V \; (5.0V \; Version) \\ 4.4V \leq V_I \leq 28V \; (3.3V \; version) \end{array} $	4.9	5.0	5.1	3.23	3.3	3.37	V
Output Voltage	V _Q	$\begin{array}{l} 100~\mu\text{A} \leq \text{I}_{Q} \leq 200~\text{mA} \\ 6.0\text{V} \leq \text{V}_{I} \leq 40\text{V (5.0V Version)} \\ 4.4\text{V} \leq \text{V}_{I} \leq 40\text{V (3.3V version)} \end{array}$	4.9	5.0	5.1	3.23	3.3	3.37	V
Output Current Limitation	ΙQ	$V_Q = 0.9 \times V_{Q,typ}$	450	700	-	450	700	-	mA
Quiescent Current	Iq	I _Q = 1.0 mA	-	140	200	-	135	200	μΑ
$I_{q} = I_{I} - I_{Q}$		I _Q = 1.0 mA, T _J = 25°C	-	140	150	_	135	150	μΑ
		I _Q = 250 mA	-	10	15	-	10	15	mA
		I _Q = 400 mA	-	23	35	-	23	35	mA
Dropout Voltage	V _{dr}	$I_Q = 300 \text{ mA}$ $V_{dr} = V_I - V_Q \text{ (Note 7)}$	-	250	500	-	1100	1170	mV
Load Regulation	ΔVQ	I _Q = 5.0 mA to 400 mA	-30	15	30	-30	15	30	mV
Line Regulation	ΔVQ	$\Delta V_{I} = 8.0 \text{ V to } 32 \text{ V},$ $I_{Q} = 5.0 \text{ mA}$	-15	5.0	15	-15	5.0	15	mV
Power Supply Ripple Rejection	PSRR	$f_r = 100 \text{ Hz}, V_r = 0.5 V_{pp}$	_	60	_	_	60	_	dB
Temperature Output Voltage Drift	dV _Q /dT		-	0.5	-	-	0.5	-	mV/K
Reset Timing D and Output RO			,	,	,	,	,	,	•
Reset Switching Threshold	V _{Q,rt}		4.53	4.65	4.8	3.0	3.1	3.2	V
Reset Output Low Voltage	V _{ROL}	$R_{ext} \ge 5.0 \text{ k}\Omega, V_Q \ge 1.0V$	-	0.2	0.4	-	0.2	0.4	٧
Reset Output Leakage Current	I _{ROH}	V _{ROH} = 5.0V	_	0	10	_	0	10	μΑ
Reset Charging Current	I _{D,C}	V _D = 1.0V	3.0	5.5	9.0	3.0	4.0	11	μΑ
Upper Timing Threshold	V _{DU}		1.5	1.8	2.2	0.7	1.3	1.6	V
Lower Timing Threshold	V _{DL}		0.2	0.4	0.7	0.2	0.4	0.7	V
Reset Delay Time	t _{rd}	C _D = 47nF	10	16	22	10	16	22	ms
Reset Reaction Time	t _{rr}	C _D = 47nF	-	1.5	4.0	-	1.5	4.0	μS
Thermal Shutdown									
Shutdown Temperature (Note 8)	T _{SD}		150	_	210	150	-	210	°C

TYPICAL PERFORMANCE CHARACTERISTICS



ESR (\O) 0.1 $V_{Q(nom)} = 3.3 V$ 0.01 100 200 IQ, OUTPUT CURRENT (mA)

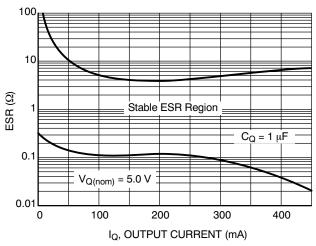
Figure 2. Output Stability with Output **Capacitor ESR**

Figure 3. Output Stability with Output **Capacitor ESR**

3.3 V Version

Stable ESR Region

 $C_Q = 22 \mu F$



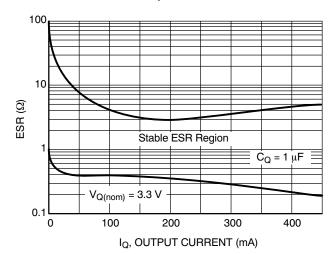
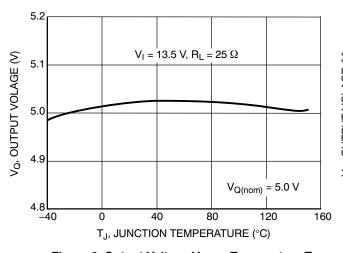


Figure 4. Output Stability with Output Capacitor ESR

Figure 5. Output Stability with Output **Capacitor ESR**



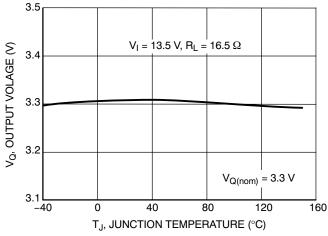
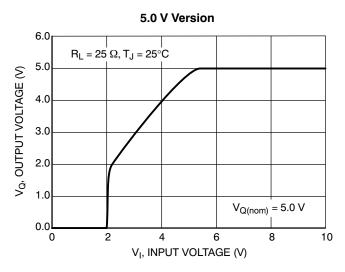


Figure 6. Output Voltage VQ vs. Temperature TJ

Figure 7. Output Voltage V_Q vs. Temperature T_J

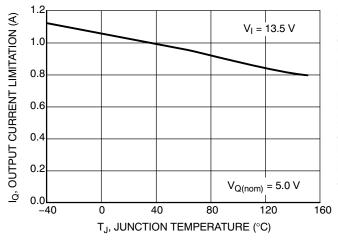
TYPICAL PERFORMANCE CHARACTERISTICS



3.3 V Version 6.0 $R_L=16.5~\Omega, T_J=25^{\circ}C$ 5.0 VQ, OUTPUT VOLTAGE (V) 4.0 3.0 2.0 1.0 $V_{Q(nom)} = 3.3 V$ 0.0 0 2 6 8 10 V_I, INPUT VOLTAGE (V)

Figure 8. Output Voltage V_Q vs. Input Voltage V_I

Figure 9. Output Voltage V_Q vs. Input Voltage V_I



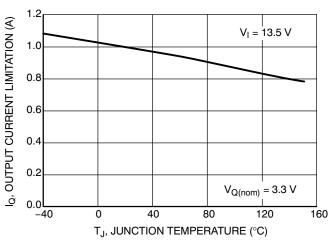
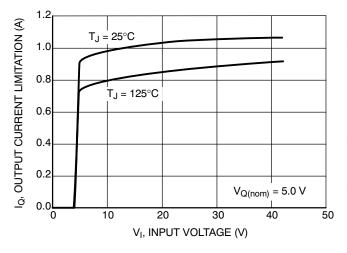


Figure 10. Output Current I_Q vs. Temperature T_J

Figure 11. Output Current I_Q vs. Temperature T_J



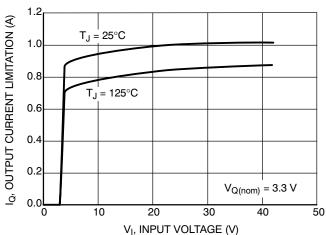
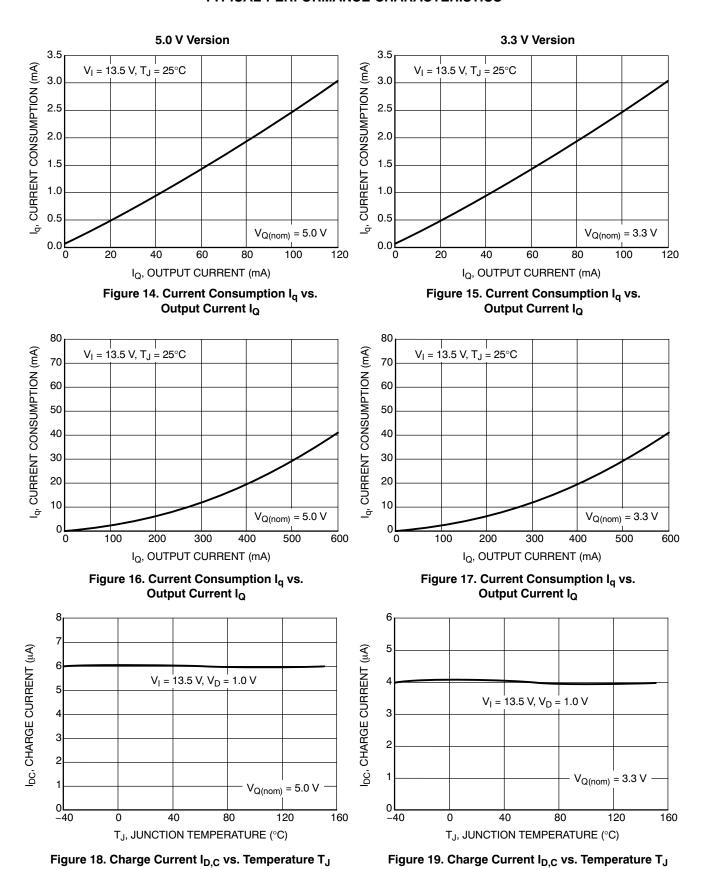


Figure 12. Output Current IQ vs. Input Voltage VI

Figure 13. Output Current I_Q vs. Input Voltage V_I

TYPICAL PERFORMANCE CHARACTERISTICS



http://onsemi.com

TYPICAL PERFORMANCE CHARACTERISTICS

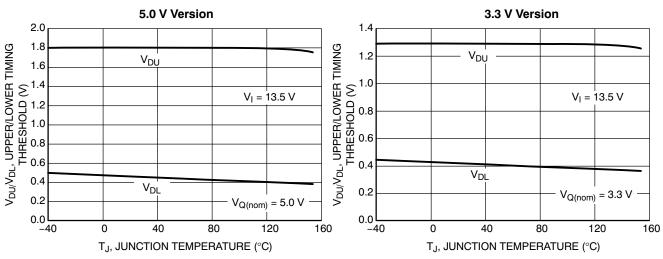


Figure 20. Delay Switching Threshold $\rm V_{DU}, \rm V_{DL}$ vs. Temperature $\rm T_{J}$

Figure 21. Delay Switching Threshold V_{DU}, V_{DL} vs. Temperature T_J

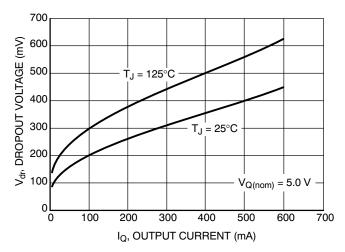


Figure 22. Drop Voltage V_{dr} vs. Output Current I_Q

APPLICATION INFORMATION

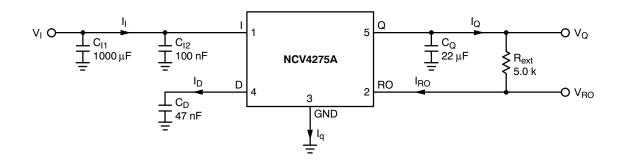


Figure 23. Test Circuit

Circuit Description

The NCV4275A is an integrated low dropout regulator that provides 5.0 V or 3.3 V, 450 mA protected output and a signal for power on reset. The regulation is provided by a PNP pass transistor controlled by an error amplifier with a bandgap reference, which gives it the lowest possible drop out voltage and best possible temperature stability. The output current capability is 450 mA, and the base drive quiescent current is controlled to prevent over saturation when the input voltage is low or when the output is overloaded. The regulator is protected by both current limit and thermal shutdown. Thermal shutdown occurs above 150°C to protect the IC during overloads and extreme ambient temperatures. The delay time for the reset output is adjustable by selection of the timing capacitor. See Figure 23, Test Circuit, for circuit element nomenclature illustration.

Regulator

The error amplifier compares the reference voltage to a sample of the output voltage (V_Q) and drives the base of a PNP series pass transistor by a buffer. The reference is a bandgap design to give it a temperature–stable output. Saturation control of the PNP is a function of the load current and input voltage. Over saturation of the output power device is prevented, and quiescent current in the ground pin is minimized.

Regulator Stability Considerations

The input capacitors (C_{I1} and C_{I2}) are necessary to stabilize the input impedance to avoid voltage line influences. Using a resistor of approximately 1.0 Ω in series with C_{I2} can stop potential oscillations caused by stray inductance and capacitance.

The output capacitor helps determine three main characteristics of a linear regulator: startup delay, load transient response and loop stability. The capacitor value and type should be based on cost, availability, size and temperature constraints. A tantalum, aluminum or ceramic capacitors can be used. The range of stability versus capacitance, load current and capacitive ESR is illustrated in Figures 2 to 5. Minimum ESR for $C_Q = 22~\mu F$ is native

ESR of ceramic capacitors. The aluminum electrolytic capacitor is the least expensive solution, but, if the circuit operates at low temperatures (-25°C to -40°C), both the capacitance and ESR of the capacitor will vary considerably. The capacitor manufacturer's data sheet usually provides this information.

The value for the output capacitor C_Q shown in Figure 23, Test Circuit, should work for most applications; however, it is not necessarily the optimized solution. Stability is guaranteed for $C_Q \ge 22 \ \mu F$ and an ESR $\le 4.5 \ \Omega$ (5.0 V Version), 3.5 Ω (3.3 V Version).

ESR characteristics were measured with ceramic capacitors and additional resistors to emulate ESR. Murata ceramic capacitors were used, GRM32ER71A226ME20 (22 μ F, 10 V, X7R, 1210), GRM31MR71E105KA01 (1 μ F, 25 V, X7R, 1206).

Reset Output

The reset output is used as the power on indicator to the microcontroller. This signal indicates when the output voltage is suitable for reliable operation of the controller. It pulls low when the output is not considered to be ready. RO is pulled up to V_Q by an external resistor, typically 5.0 k Ω in value. The input and output conditions that control the Reset Output and the relative timing are illustrated in Figure 24, Reset Timing.

Output voltage regulation must be maintained for the delay time before the reset output signals a valid condition. The delay for the reset output is defined as the amount of time it takes the timing capacitor on the delay pin to charge from a residual voltage of 0.0 V to the upper timing threshold voltage V_{DU} . The charging current for this is $I_{D,C}$ and D pin voltage in steady state is typically 3.2 V for 5.0 V regulator and typically 2.4 V for 3.3 V regulator. By using typical IC parameters with a 47 nF capacitor on the D pin, the following time delay for 5.0 V regulator is derived:

$$t_{RD} = C_D V_{DU} / I_{D,C}$$

$$t_{RD} = 47 \text{ nF} (1.8 \text{ V}) / 5.5 \mu A = 15.4 \text{ ms}$$

Other time delays can be obtained by changing the capacitor value.

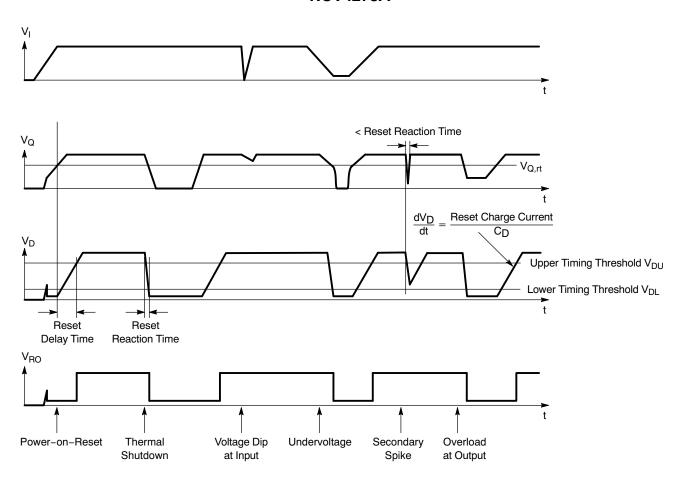


Figure 24. Reset Timing

Calculating Power Dissipation in a Single Output Linear Regulator

The maximum power dissipation for a single output regulator (Figure 25) is:

$$PD(max) = [VI(max) - VQ(min)] IQ(max) + VI(max)Iq$$
(1)

where

 $\begin{array}{ll} V_{I(max)} & \text{is the maximum input voltage,} \\ V_{Q(min)} & \text{is the minimum output voltage,} \end{array}$

 $I_{O(max)}$ is the maximum output current for the

application,

I_q is the quiescent current the regulator

consumes at $I_{Q(max)}$.

Once the value of $P_{D(max)}$ is known, the maximum permissible value of $R_{\theta JA}$ can be calculated:

$$R_{\theta}JA = \frac{150^{\circ}C - T_{A}}{P_{D}} \tag{2}$$

The value of $R_{\theta JA}$ can then be compared with those in the package section of the data sheet. Those packages with $R_{\theta JA}$'s less than the calculated value in Equation 2 will keep the die temperature below 150°C.

In some cases, none of the packages will be sufficient to dissipate the heat generated by the IC, and an external heatsink will be required.

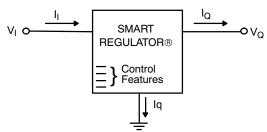


Figure 25. Single Output Regulator with Key Performance Parameters Labeled

Heatsinks

A heatsink effectively increases the surface area of the package to improve the flow of heat away from the IC and into the surrounding air.

Each material in the heat flow path between the IC and the outside environment will have a thermal resistance. Like series electrical resistances, these resistances are summed to determine the value of $R_{\theta IA}$:

$$R_{\theta JA} = R_{\theta JC} + R_{\theta CS} + R_{\theta SA}$$
 (3)

where

 $\begin{array}{ll} R_{\theta JC} & \text{is the junction-to-case thermal resistance,} \\ R_{\theta CS} & \text{is the case-to-heatsink thermal resistance,} \\ R_{\theta SA} & \text{is the heatsink-to-ambient thermal} \end{array}$

resistance.

 $R_{\theta JC}$ appears in the package section of the data sheet. Like $R_{\theta JA}$, it too is a function of package type. $R_{\theta CS}$ and $R_{\theta SA}$ are functions of the package type, heatsink and the interface between them. These values appear in heatsink data sheets of heatsink manufacturers.

Thermal, mounting, and heatsinking considerations are discussed in the ON Semiconductor application note AN1040/D.

Thermal Model

A discussion of thermal modeling is in the ON Semiconductor web site: http://www.onsemi.com/pub/collateral/BR1487-D.PDF.

Table 1. DPAK 5-Lead Thermal RC Network Models

Drain Co	pper Area (1	oz thick)	168 mm ²	736 mm ²		168 mm ²	736 mm ²	
(SPI	ICE Deck Fo	rmat)	Cauer N	Network		Foster	Network	
			168 mm ²	736 mm ²	Units	Tau	Tau	Units
C_C1	Junction	Gnd	1.00E-06	1.00E-06	W-s/C	1.36E-08	1.361E-08	sec
C_C2	node1	Gnd	1.00E-05	1.00E-05	W-s/C	7.41E-07	7.411E-07	sec
C_C3	node2	Gnd	6.00E-05	6.00E-05	W-s/C	1.04E-05	1.029E-05	sec
C_C4	node3	Gnd	1.00E-04	1.00E-04	W-s/C	3.91E-05	3.737E-05	sec
C_C5	node4	Gnd	4.36E-04	3.64E-04	W-s/C	1.80E-03	1.376E-03	sec
C_C6	node5	Gnd	6.77E-02	1.92E-02	W-s/C	3.77E-01	2.851E-02	sec
C_C7	node6	Gnd	1.51E-01	1.27E-01	W-s/C	3.79E+00	9.475E-01	sec
C_C8	node7	Gnd	4.80E-01	1.018	W-s/C	2.65E+01	1.173E+01	sec
C_C9	node8	Gnd	3.740	2.955	W-s/C	8.71E+01	8.59E+01	sec
C_C10	node9	Gnd	10.322	0.438	W-s/C			sec
			168 mm ²	736 mm ²		R's	R's	
R_R1	Junction	node1	0.015	0.015	C/W	0.0123	0.0123	C/W
R_R2	node1	node2	0.08	0.08	C/W	0.0585	0.0585	C/W
R_R3	node2	node3	0.4	0.4	C/W	0.0304	0.0287	C/W
R_R4	node3	node4	0.2	0.2	C/W	0.3997	0.3772	C/W
R_R5	node4	node5	2.97519	2.6171	C/W	3.115	2.68	C/W
R_R6	node5	node6	8.2971	1.6778	C/W	3.571	1.38	C/W
R_R7	node6	node7	25.9805	7.4246	C/W	12.851	5.92	C/W
R_R8	node7	node8	46.5192	14.9320	C/W	35.471	7.39	C/W
R_R9	node8	node9	17.7808	19.2560	C/W	46.741	28.94	C/W
R_R10	node9	Gnd	0.1	0.1758	C/W			C/W

NOTE: Bold face items represent the package without the external thermal system.

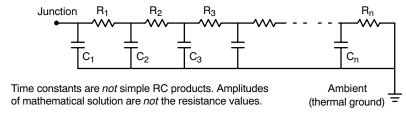


Figure 26. Grounded Capacitor Thermal Network ("Cauer" Ladder)

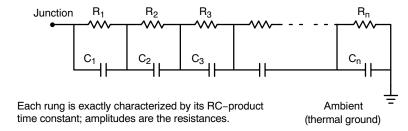


Figure 27. Non-Grounded Capacitor Thermal Ladder ("Foster" Ladder)

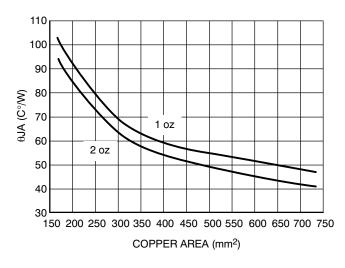
Table 2. D²PAK 5-Lead Thermal RC Network Models

Drain Co	pper Area (1	oz thick)	241 mm ²	788 mm ²		241 mm ²	788 mm ²	
(SPI	(SPICE Deck Format)		Cauer N	Network		Foster I	Network	
			241 mm ²	653 mm ²	Units	Tau	Tau	Units
C_C1	Junction	Gnd	1.00E-06	1.00E-06	W-s/C	1.361E-08	1.361E-08	sec
C_C2	node1	Gnd	1.00E-05	1.00E-05	W-s/C	7.411E-07	7.411E-07	sec
С_С3	node2	Gnd	6.00E-05	6.00E-05	W-s/C	1.005E-05	1.007E-05	sec
C_C4	node3	Gnd	1.00E-04	1.00E-04	W-s/C	3.460E-05	3.480E-05	sec
C_C5	node4	Gnd	2.82E-04	2.87E-04	W-s/C	7.868E-04	8.107E-04	sec
C_C6	node5	Gnd	5.58E-03	5.95E-03	W-s/C	7.431E-03	7.830E-03	sec
C_C7	node6	Gnd	4.25E-01	4.61E-01	W-s/C	2.786E+00	2.012E+00	sec
C_C8	node7	Gnd	9.22E-01	2.05	W-s/C	2.014E+01	2.601E+01	sec
C_C9	node8	Gnd	1.73	4.88	W-s/C	1.134E+02	1.218E+02	sec
C_C10	node9	Gnd	7.12	1.31	W-s/C			sec
			241 mm ²	653 mm ²		R's	R's	
R_R1	Junction	node1	0.015	0.0150	C/W	0.0123	0.0123	C/W
R_R2	node1	node2	0.08	0.0800	C/W	0.0585	0.0585	C/W
R_R3	node2	node3	0.4	0.4000	C/W	0.0257	0.0260	C/W
R_R4	node3	node4	0.2	0.2000	C/W	0.3413	0.3438	C/W
R_R5	node4	node5	1.85638	1.8839	C/W	1.77	1.81	C/W
R_R6	node5	node6	1.23672	1.2272	C/W	1.54	1.52	C/W
R_R7	node6	node7	9.81541	5.3383	C/W	4.13	3.46	C/W
R_R8	node7	node8	33.1868	18.9591	C/W	6.27	5.03	C/W
R_R9	node8	node9	27.0263	13.3369	C/W	60.80	29.30	C/W
R_R10	node9	gnd	1.13944	0.1191	C/W			C/W

NOTE: Bold face items represent the package without the external thermal system.

The Cauer networks generally have physical significance and may be divided between nodes to separate thermal behavior due to one portion of the network from another. The Foster networks, though when sorted by time constant (as above) bear a rough correlation with the Cauer networks, are really only convenient mathematical models. Cauer networks can be easily implemented using circuit simulating tools, whereas Foster networks may be more easily implemented using mathematical tools (for instance, in a spreadsheet program), according to the following formula:

$$R(t) = \sum_{i=1}^{n} R_i (1-e^{-t/tau_i})$$



110 90 80 70 60 2 oz 150 200 250 300 350 400 450 500 550 600 650 700 750 COPPER AREA (mm²)

Figure 28. θ JA vs. Copper Spreader Area, DPAK 5-Lead

Figure 29. θ JA vs. Copper Spreader Area, D²PAK 5-Lead

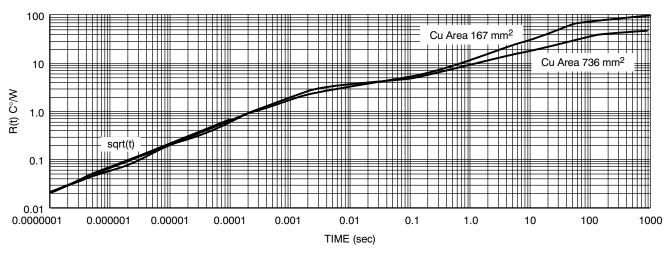


Figure 30. Single-Pulse Heating Curves, DPAK 5-Lead

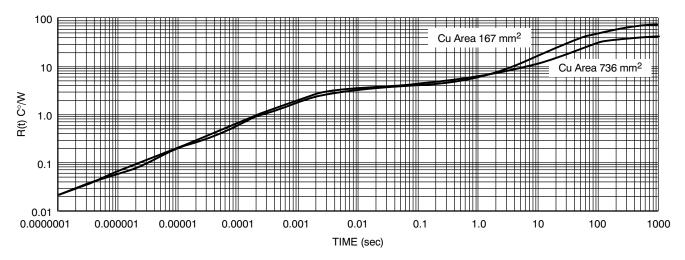


Figure 31. Single-Pulse Heating Curves, D2PAK 5-Lead

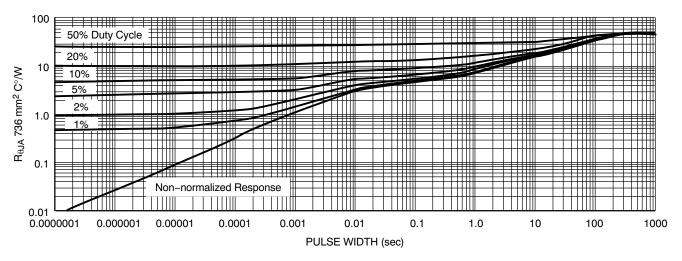


Figure 32. Duty Cycle for 1" Spreader Boards, DPAK 5-Lead

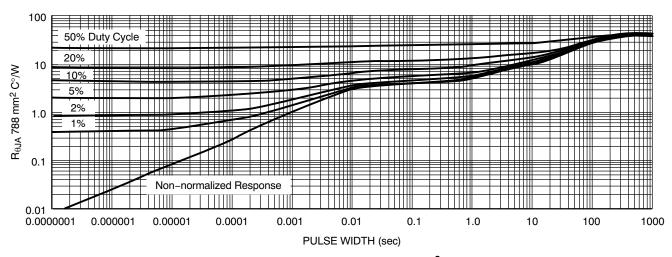


Figure 33. Duty Cycle for 1" Spreader Boards, D2PAK 5-Lead

EMC-Characteristics: Conducted Susceptibility

All EMC-Characteristics are based on limited samples and no part of production test according to 47A/658/CD IEC62132-4 (direct Power Injection).

Test Conditions

Supply Voltage $V_{in} = 12 \text{ V}$

Temperature $T_A = 23^{\circ}C \pm 5^{\circ}C$

Load $R_L = 100 \Omega$

Direct Power Injection

33 dBm (Note 1) forward power CW for global pin (Note 2) 17 dBm (Note 1) forward power CW for local pin (Note 3)

Acceptance Criteria

Amplitude Dev. max 4% of Output Voltage Reset outputs remain in correct state ±1 V

- 1. dBm means dB mili-Watts, P(dBm) = 10 log (P(mW)).
- 2. A global pin carries a signal or power which enters or leaves the application board.
- A local pin carries a signal or power which does not leave the application board. It remains on the application board as a signal between two components.

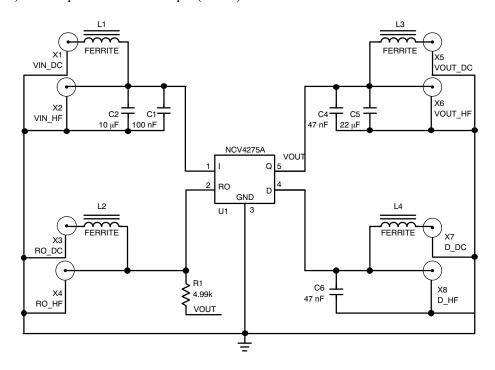


Figure 34. Test Circuit

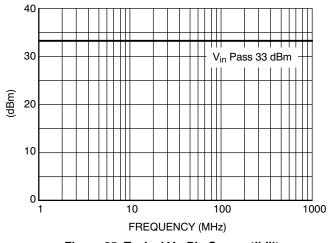


Figure 35. Typical V_{in} Pin Susceptibility

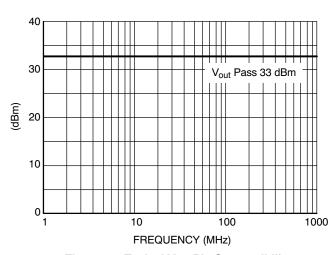


Figure 36. Typical Vout Pin Susceptibility

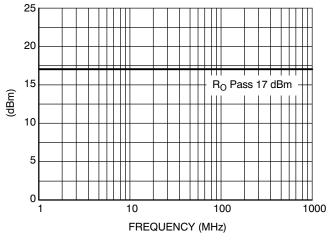


Figure 37. Typical R_{O} Pin Susceptibility

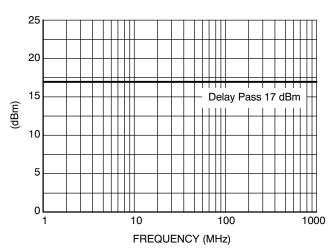


Figure 38. Typical Delay Pin Susceptibility

ORDERING INFORMATION

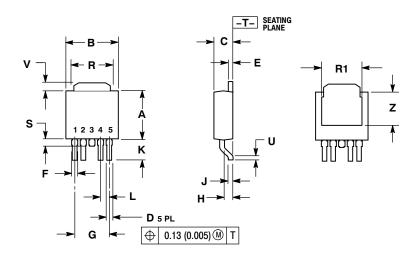
Device	Output Voltage	Package	Shipping [†]
NCV4275ADS50G	5.0 V	D ² PAK	50 Units/Rail
NCV4275ADS50R4G		(Pb-Free)	800 Tape & Reel
NCV4275ADT50RKG		DPAK (Pb-Free)	2500 Tape & Reel
NCV4275ADS33G	3.3 V	D ² PAK	50 Units/Rail
NCV4275ADS33R4G		(Pb-Free)	800 Tape & Reel
NCV4275ADT33RKG		DPAK (Pb-Free)	2500 Tape & Reel

[†]For information on tape and reel specifications,including part orientation and tape sizes, please refer to our Tape and Reel Packaging Specifications Brochure, BRD8011/D.

PACKAGE DIMENSIONS

DPAK 5, CENTER LEAD CROP DT SUFFIX

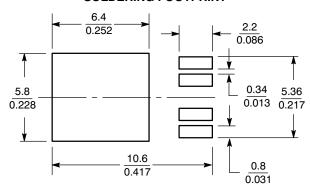
CASE 175AA-01 ISSUE A



- NOTES: 1. DIMENSIONING AND TOLERANCING PER ANSI Y14.5M, 1982. 2. CONTROLLING DIMENSION: INCH.

	INC	HES	MILLIN	IETERS	
DIM	MIN	MAX	MIN	MAX	
Α	0.235	0.245	5.97	6.22	
В	0.250	0.265	6.35	6.73	
С	0.086	0.094	2.19	2.38	
D	0.020	0.028	0.51	0.71	
Е	0.018	0.023	0.46	0.58	
F	0.024	0.032	0.61	0.81	
G	0.180	BSC	4.56 BSC		
Н	0.034	0.040	0.87	1.01	
J	0.018	0.023	0.46	0.58	
K	0.102	0.114	2.60	2.89	
L	0.045	BSC	1.14	BSC	
R	0.170	0.190	4.32	4.83	
R1	0.185	0.210	4.70	5.33	
S	0.025	0.040	0.63	1.01	
U	0.020		0.51		
٧	0.035	0.050	0.89	1.27	
Z	0.155	0.170	3.93	4.32	

SOLDERING FOOTPRINT*

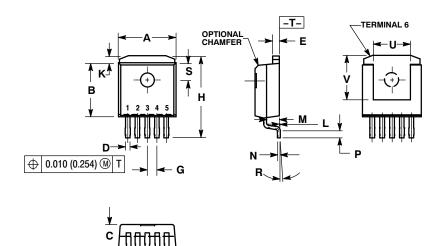


SCALE 4:1

^{*}For additional information on our Pb-Free strategy and soldering details, please download the ON Semiconductor Soldering and Mounting Techniques Reference Manual, SOLDERRM/D.

PACKAGE DIMENSIONS

D²PAK, 5 LEAD **DS SUFFIX** CASE 936A-02 **ISSUE C**

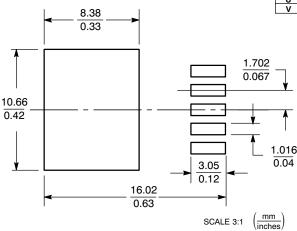


NOTES

- DIMENSIONING AND TOLERANCING PER ANSI Y14.5M, 1982. CONTROLLING DIMENSION: INCH.
- 3. TAB CONTOUR OPTIONAL WITHIN DIMENSIONS A AND K.
- DIMENSIONS U AND V ESTABLISH A MINIMUM MOUNTING SURFACE FOR TERMINAL 6.
- DIMENSIONS A AND B DO NOT INCLUDE MOLD FLASH OR GATE PROTRUSIONS. MOLD FLASH AND GATE PROTRUSIONS NOT TO EXCEED 0.025 (0.635) MAXIMUM.

	INC	HES	MILLIN	IETERS	
DIM	MIN	MAX	MIN	MAX	
Α	0.386	0.403	9.804	10.236	
В	0.356	0.368	9.042	9.347	
С	0.170	0.180	4.318	4.572	
D	0.026	0.036	0.660	0.914	
E	0.045	0.055	1.143	1.397	
G	0.067	BSC	1.702	BSC	
Н	0.539	0.579	13.691	14.707	
K	0.050	REF	1.270 REF		
L	0.000	0.010	0.000	0.254	
M	0.088	0.102	2.235	2.591	
N	0.018	0.026	0.457	0.660	
Р	0.058	0.078	1.473	1.981	
R	5 ° F	REF	5° F	REF	
S	0.116	REF	2.946	REF	
U	0.200	MIN	5.080	MIN (
V	0.250	MIN	6.350	MIN (

SOLDERING FOOTPRINT*



*For additional information on our Pb-Free strategy and soldering details, please download the ON Semiconductor Soldering and Mounting Techniques Reference Manual, SOLDERRM/D.

ON Semiconductor and are registered trademarks of Semiconductor Components Industries, LLC (SCILLC). SCILLC reserves the right to make changes without further notice to any products herein. SCILLC makes no warranty, representation or guarantee regarding the suitability of its products for any particular purpose, nor does SCILLC assume any liability arising out of the application or use of any product or circuit, and specifically disclaims any and all liability, including without limitation special, consequential or incidental damages. "Typical" parameters which may be provided in SCILLC data sheets any/or specifications can and do vary in different applications and actual performance may vary over time. All operating parameters, including "Typicals" must be validated for each customer application by customer's technical experts. SCILLC does not convey any license under its patent rights nor the rights of others. SCILLC products are not designed, intended, or authorized for use as components in systems intended for surgical implant into the body, or other applications intended to support or sustain life, or for any other application in which the failure of the SCILLC product could create a situation where personal injury or death may occur. Should Buyer purchase or use SCILLC products for any such unintended or unauthorized application, Buyer shall indemnify and hold SCILLC and its officers, employees, subsidiaries, affiliates, and distributors harmless against all claims, costs, damages, and expenses, and reasonable attorney fees arising out of, directly or indirectly, any claim of personal injury or death associated with such unintended or unauthorized use, even if such claim alleges that SCILLC was negligent regarding the design or manufacture of the part. SCILLC is an Equal Opportunity/Affirmative Action Employer. This literature is subject to all applicable copyright laws and is not for resale in any manner.

PUBLICATION ORDERING INFORMATION

LITERATURE FULFILLMENT:

Literature Distribution Center for ON Semiconductor P.O. Box 5163, Denver, Colorado 80217 USA Phone: 303-675-2175 or 800-344-3860 Toll Free USA/Canada Fax: 303-675-2176 or 800-344-3867 Toll Free USA/Canada Email: orderlit@onsemi.com

N. American Technical Support: 800-282-9855 Toll Free USA/Canada

Europe, Middle East and Africa Technical Support: Phone: 421 33 790 2910

Japan Customer Focus Center Phone: 81-3-5773-3850

ON Semiconductor Website: www.onsemi.com

Order Literature: http://www.onsemi.com/orderlit

For additional information, please contact your local Sales Representative